

July 2007

MPSA13

NPN Darlington Transistor

- This device is designed for applications requiring extremely high Current gain at collector Currents to 1.0A.
- Sourced from process 05.



1. Emitter 2. Base 3. Collector

Absolute Maximum Ratings $T_a = 25$ °C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CES}	Collector-Emitter Voltage	30	V	
V _{CBO}	Collector-Base Voltage	30		
V _{EBO}	Emitter-Base Voltage	10	V	
I _C	Collector Current - Continuous	1.2	А	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units			
Off Charac	Off Characteristics							
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	$I_C = 100 \mu A, I_B = 0$	30		V			
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 30V, I_{E} = 0$		100	nA			
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 10V, I_{C} = 0$		100	nA			
On Characteristics *								
h _{FE}	DC Current Gain	$V_{CE} = 5.0V, I_{C} = 10mA$ $V_{CE} = 5.0, I_{C} = 100mA$	5,000 10,000					
V _{CE (sat)}	Collector-Emitter Saturation Voltage	I _C = 100mA, I _B = 0.1mA		1.5	V			
V _{BE (on)}	Base-Emitter On Voltage	$I_C = 100 \text{mA}, V_{CE} = 5.0 \text{V}$		2.0	V			
Small Signal Characteristics								
f _T	Current Gain Bandwidth Product	I _C = 10mA, V _{CE} = 10V, f = 100MHz	125		pF			

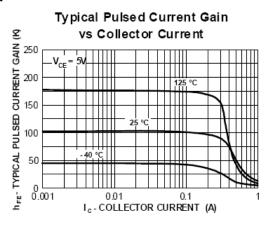
^{*} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%

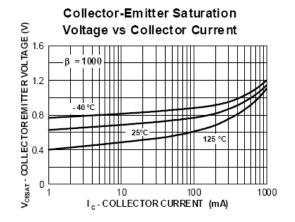
Thermal Characteristics T_a=25°C unless otherwise noted

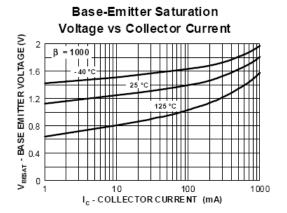
Symbol	Parameter	Max.	Units
P_{D}	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

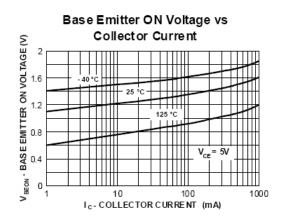
^{*} Device mounted on FR-4PCB 1.6" \times 1.6" \times 0.06".

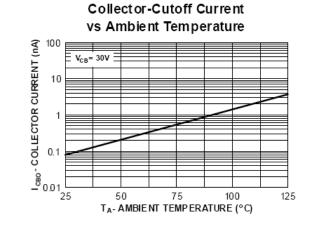
Typical Characteristics

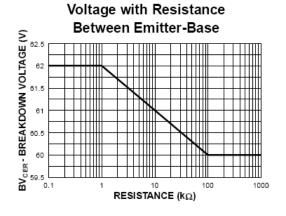








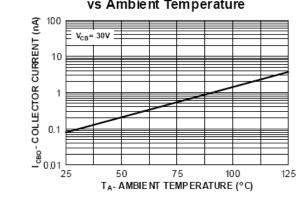




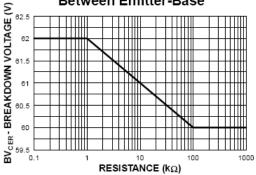
Collector-Emitter Breakdown

Typical Characteristics (continued)

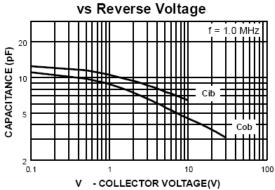
Collector-Cutoff Current vs Ambient Temperature



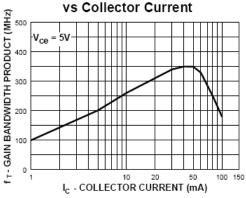
Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base



Input and Output Capacitance

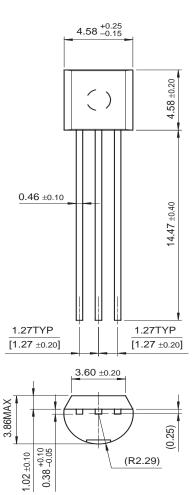


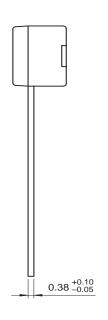
Gain Bandwidth Product



Mechanical Dimensions

TO-92





Dimensions in Millimeters





TinyBoost™

TinvBuck™

TinyLogic[®]
TINYOPTO™

TinvPower™

TruTranslation™

TinyWire™

μSerDes™

UniFET™

UHC®

 VCX^{TM}

Wire™

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